



Bipolar NPN Bare Die – BTN491

Part Description

The BTN491 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 35V
- VCEO = 30V
- VEBO = 4V
- hFE = 36-265 @ VCE = 12V, IC = 0.002A
- VCE(Sat) = 0.4V @ IC = 0.01A, IB = 1mA
- fT = 100 MHz @ VCE = 10V, IE = 0A
- COBO = 3pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to TOSHIBA 2SC380 and ROHM 2SC2058S

Die Size (Unawn)

400µm X 400µm, 16 Mils X 16 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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